# MAC223A6

## 4Q Triac

15 September 2018 Product data sheet

## 1. General description

Planar passivated four quadrant triac in a SOT78 (T0-220AB) plastic package intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance.

## 2. Features and benefits

- High blocking voltage capability
- High noise immunity
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants

## 3. Applications

- General purpose motor controls
- General purpose switching

## 4. Quick reference data

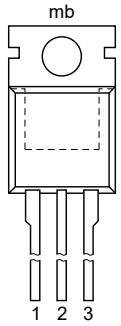
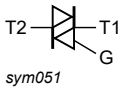
**Table 1. Quick reference data**

| Symbol | Parameter | Conditions | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| $V_{DRM}$ | repetitive peak off-state voltage | | | - | - | 400 | V |
| $I_{T(RMS)}$ | RMS on-state current | full sine wave; $T_{mb} \leq 91$ °C; Fig. 1; Fig. 2; Fig. 3 | | - | - | 25 | A |
| $I_{TSM}$ | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25$ °C; $t_p = 20$ ms; Fig. 4; Fig. 5 | | - | - | 190 | A |
| | | full sine wave; $T_{j(init)} = 25$ °C; $t_p = 16.7$ ms | | - | - | 230 | A |
| $T_j$ | junction temperature | | | - | - | 125 | °C |
| **Static characteristics** | | | | | | | |
| $I_{GT}$ | gate trigger current | $V_D = 12$ V; $I_T = 0.1$ A; T2+ G+; $T_j = 25$ °C; Fig. 7 | | - | 6 | 50 | mA |
| | | $V_D = 12$ V; $I_T = 0.1$ A; T2+ G-; $T_j = 25$ °C; Fig. 7 | | - | 10 | 50 | mA |
| | | $V_D = 12$ V; $I_T = 0.1$ A; T2- G-; $T_j = 25$ °C; Fig. 7 | | - | 11 | 50 | mA |
| | | $V_D = 12$ V; $I_T = 0.1$ A; T2- G+; $T_j = 25$ °C; Fig. 7 | | - | 23 | 75 | mA |
| $I_H$ | holding current | $V_D = 12$ V; $T_j = 25$ °C; T2+; Fig. 9 | | - | 7 | 30 | mA |

| Symbol | Parameter | Conditions | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| | | $V_D$ = 12 V; $T_j$ = 25 °C; T2-; Fig. 9 | | - | 12 | 30 | mA |
| $V_T$ | on-state voltage | $I_T$ = 30 A; $T_j$ = 25 °C; Fig. 10 | | - | 1.3 | 1.55 | V |
| **Dynamic characteristics** | | | | | | | |
| $dV_D/dt$ | rate of rise of off-state voltage | $V_{DM}$ = 268 V; $T_j$ = 125 °C; ($V_{DM}$ = 67% of $V_{DRM}$); exponential waveform; gate open circuit | | 100 | 300 | - | V/µs |
| $dV_{com}/dt$ | rate of change of commutating voltage | $V_D$ = 400 V; $T_j$ = 95 °C; $dI_{com}/dt$ = 9 A/ms; $I_T$ = 25 A; gate open circuit | | - | 10 | - | V/µs |

## 5. Pinning information

**Table 2. Pinning information**

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|---|---|---|---|---|
| 1 | T1 | main terminal 1 |  **TO-220AB (SOT78)** |  *sym051* |
| 2 | T2 | main terminal 2 | | |
| 3 | G | gate | | |
| mb | T2 | mounting base; main terminal 2 | | |

## 6. Ordering information

**Table 3. Ordering information**

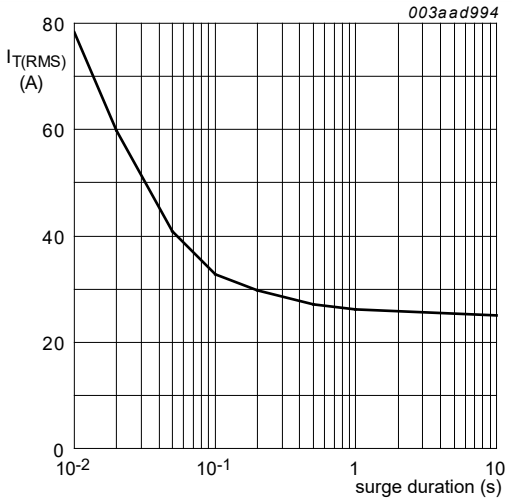
| Type number | Package | | |
|---|---|---|---|
| | Name | Description | Version |
| MAC223A6 | TO-220AB | plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB | SOT78 |

# 7. Limiting values

**Table 4. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|---|---|---|---|---|---|---|
| $V_{DRM}$ | repetitive peak off-state voltage | | | - | 400 | V |
| $I_{T(RMS)}$ | RMS on-state current | full sine wave; $T_{mb} \leq 91$ °C; Fig. 1; Fig. 2; Fig. 3 | | - | 25 | A |
| $I_{TSM}$ | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25$ °C; $t_p = 20$ ms; Fig. 4; Fig. 5 | | - | 190 | A |
| | | full sine wave; $T_{j(init)} = 25$ °C; $t_p = 16.7$ ms | | - | 230 | A |
| $I^2t$ | $I^2t$ for fusing | $t_p = 10$ ms; SIN | | - | 180 | $A^2s$ |
| $dI_T/dt$ | rate of rise of on-state current | $I_G = 200$ mA; T2+ G+ | | - | 50 | A/µs |
| | | $I_G = 200$ mA; T2+ G- | | - | 50 | A/µs |
| | | $I_G = 200$ mA; T2- G- | | - | 50 | A/µs |
| | | $I_G = 200$ mA; T2- G+ | | - | 10 | A/µs |
| $I_{GM}$ | peak gate current | | | - | 2 | A |
| $P_{GM}$ | peak gate power | | | - | 5 | W |
| $P_{G(AV)}$ | average gate power | over any 20 ms period | | - | 0.5 | W |
| $T_{stg}$ | storage temperature | | | -40 | 150 | °C |
| $T_j$ | junction temperature | | | - | 125 | °C |




f = 50 Hz; $T_{mb}$ = 91 °C

**Fig. 1. RMS on-state current as a function of surge duration; maximum values**

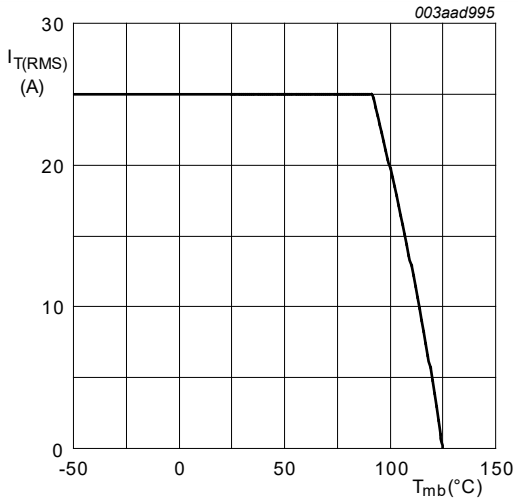
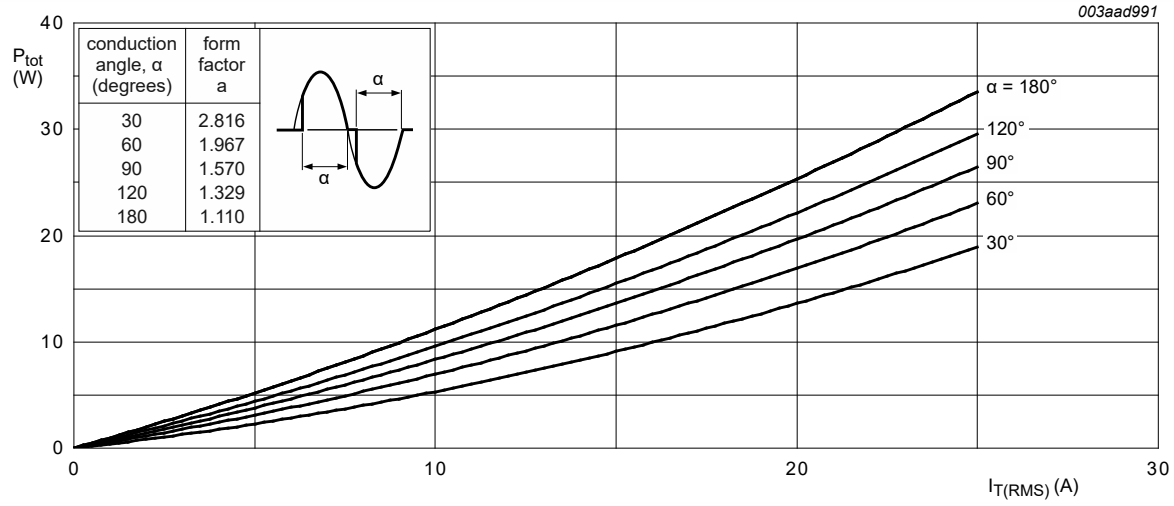


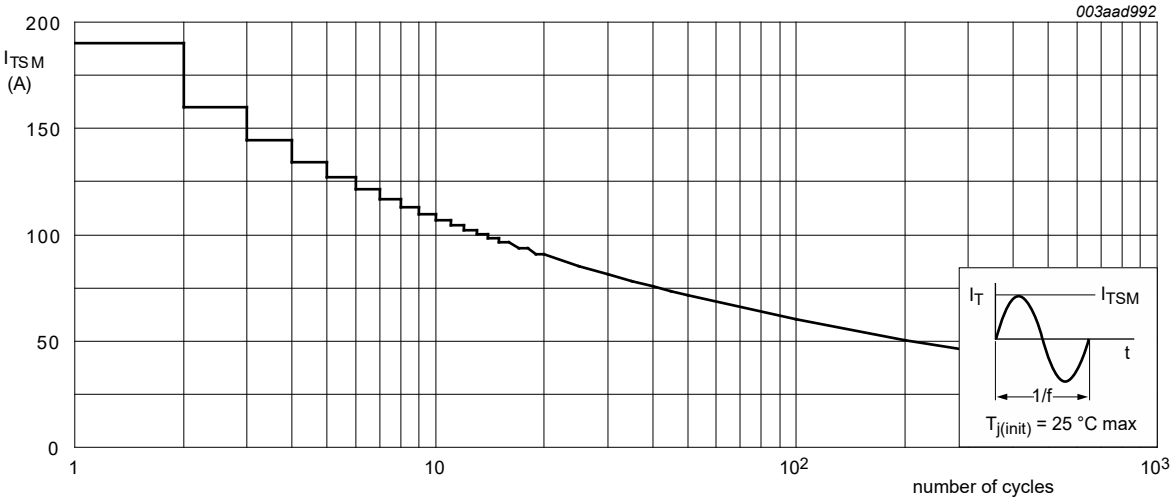

**Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values**




α = conduction angle

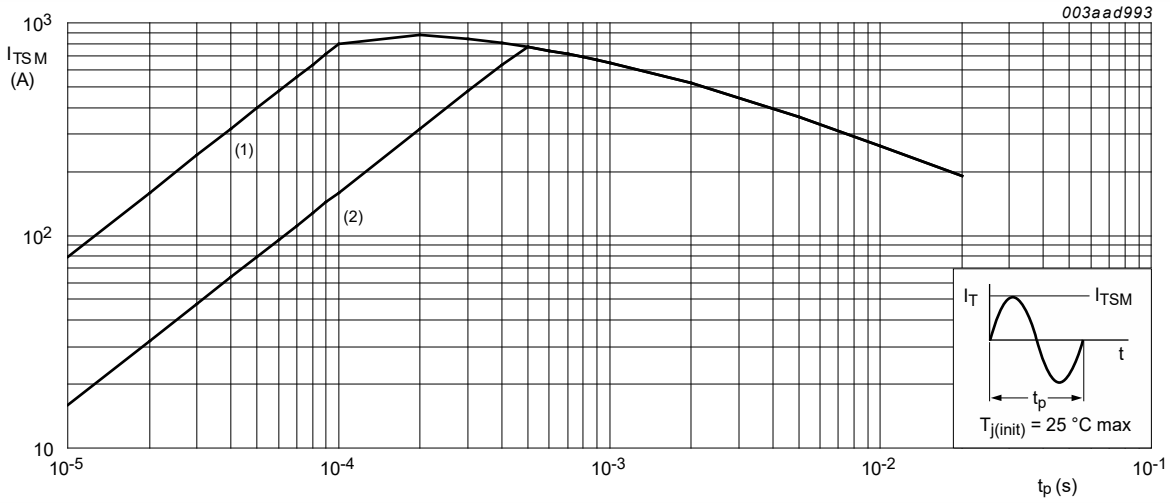
a = form factor = $I_{T(RMS)}$ / $I_{T(AV)}$

**Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values**




f = 50 Hz

**Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values**



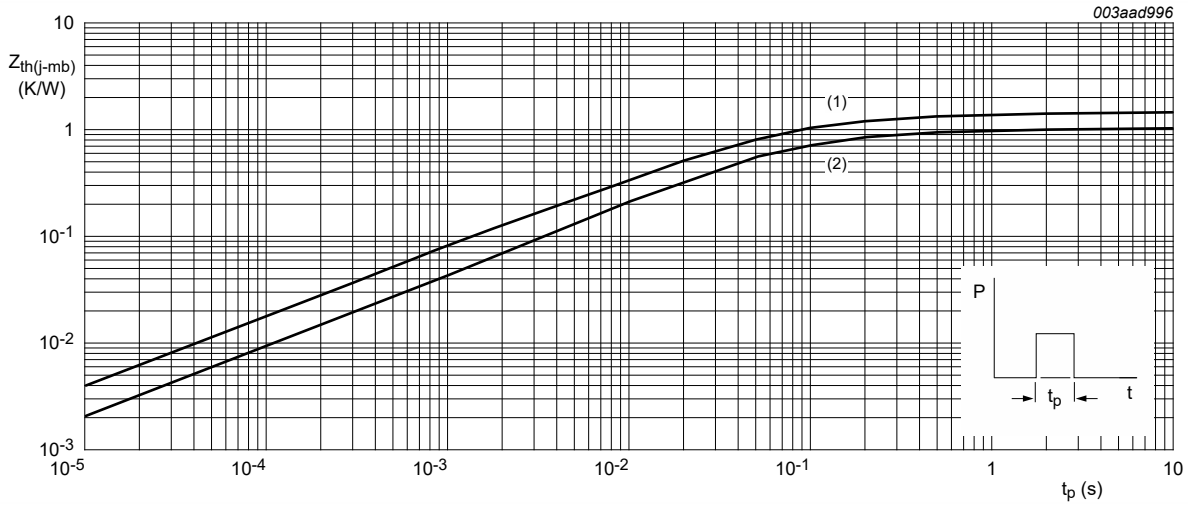

$t_p \leq 20$ ms
(1) $dI_T/dt$ limit
(2) T2- G+ quadrant limit

**Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values**

# 8. Thermal characteristics

**Table 5. Thermal characteristics**

| Symbol | Parameter | Conditions | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | full cycle; Fig. 6 | | - | - | 1 | K/W |
| | | half cycle; Fig. 6 | | - | - | 1.4 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient free air | in free air | | - | 60 | - | K/W |



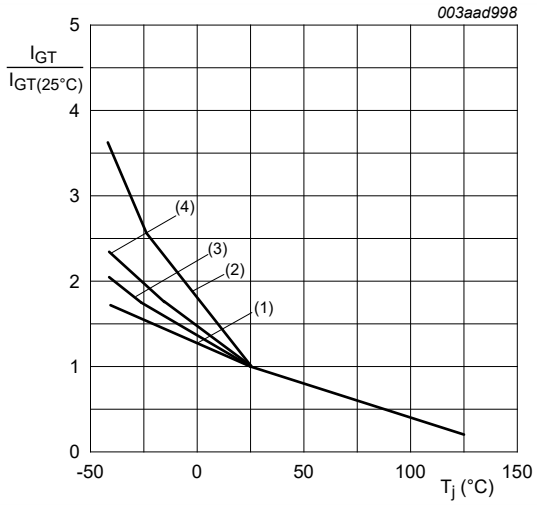

(1) Unidirectional (half cycle)
(2) Bidirectional (full cycle)

**Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width**

# 9. Characteristics

**Table 6. Characteristics**

| Symbol | Parameter | Conditions | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| **Static characteristics** | | | | | | | |
| $I_{GT}$ | gate trigger current | $V_D$ = 12 V; $I_T$ = 0.1 A; T2+ G+; $T_j$ = 25 °C; Fig. 7 | | - | 6 | 50 | mA |
| | | $V_D$ = 12 V; $I_T$ = 0.1 A; T2+ G-; $T_j$ = 25 °C; Fig. 7 | | - | 10 | 50 | mA |
| | | $V_D$ = 12 V; $I_T$ = 0.1 A; T2- G-; $T_j$ = 25 °C; Fig. 7 | | - | 11 | 50 | mA |
| | | $V_D$ = 12 V; $I_T$ = 0.1 A; T2- G+; $T_j$ = 25 °C; Fig. 7 | | - | 23 | 75 | mA |
| $I_L$ | latching current | $V_D$ = 12 V; $I_G$ = 0.1 A; T2+ G+; $T_j$ = 25 °C; Fig. 8 | | - | 8 | 40 | mA |
| | | $V_D$ = 12 V; $I_G$ = 0.1 A; T2+ G-; $T_j$ = 25 °C; Fig. 8 | | - | 30 | 60 | mA |
| | | $V_D$ = 12 V; $I_G$ = 0.1 A; T2- G-; $T_j$ = 25 °C; Fig. 8 | | - | 18 | 40 | mA |
| | | $V_D$ = 12 V; $I_G$ = 0.1 A; T2- G+; $T_j$ = 25 °C; Fig. 8 | | - | 15 | 60 | mA |
| $I_H$ | holding current | $V_D$ = 12 V; $T_j$ = 25 °C; T2+; Fig. 9 | | - | 7 | 30 | mA |
| | | $V_D$ = 12 V; $T_j$ = 25 °C; T2-; Fig. 9 | | - | 12 | 30 | mA |
| $V_T$ | on-state voltage | $I_T$ = 30 A; $T_j$ = 25 °C; Fig. 10 | | - | 1.3 | 1.55 | V |
| $V_{GT}$ | gate trigger voltage | $V_D$ = 12 V; $I_T$ = 0.1 A; $T_j$ = 25 °C; Fig. 11 | | - | 0.7 | 1 | V |
| | | $V_D$ = 400 V; $I_T$ = 0.1 A; $T_j$ = 125 °C; Fig. 11 | | 0.25 | 0.4 | - | V |
| $I_D$ | off-state current | $V_D$ = 400 V; $T_j$ = 125 °C | | - | 0.1 | 0.5 | mA |
| **Dynamic characteristics** | | | | | | | |
| $dV_D/dt$ | rate of rise of off-state voltage | $V_{DM}$ = 268 V; $T_j$ = 125 °C; ($V_{DM}$ = 67% of $V_{DRM}$); exponential waveform; gate open circuit | | 100 | 300 | - | V/µs |
| $dV_{com}/dt$ | rate of change of commutating voltage | $V_D$ = 400 V; $T_j$ = 95 °C; $dI_{com}/dt$ = 9 A/ms; $I_T$ = 25 A; gate open circuit | | - | 10 | - | V/µs |
| $t_{gt}$ | gate-controlled turn-on time | $I_{TM}$ = 30 A; $V_D$ = 400 V; $I_G$ = 0.1 A; $dI_G/dt$ = 5 A/µs | | - | 2 | - | µs |




(1) T2+ G+
(2) T2+ G-
(3) T2- G-
(4) T2- G+

**Fig. 7. Normalized gate trigger current as a function of junction temperature**

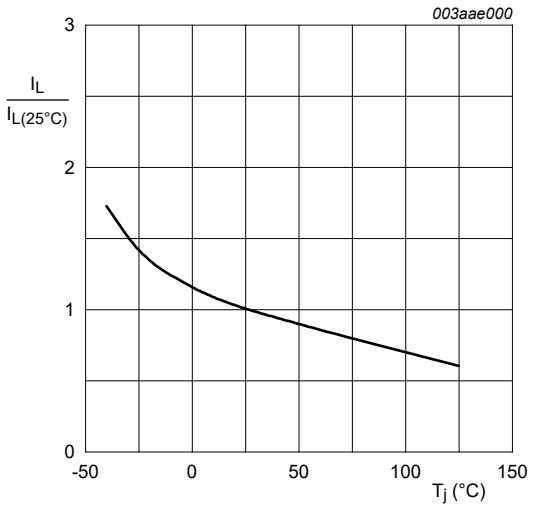



**Fig. 8. Normalized latching current as a function of junction temperature**

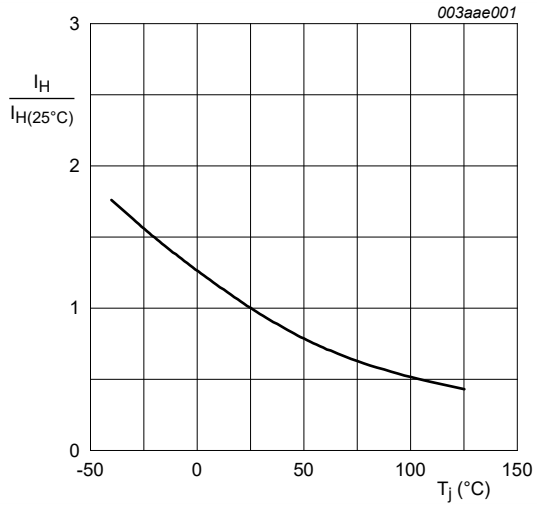
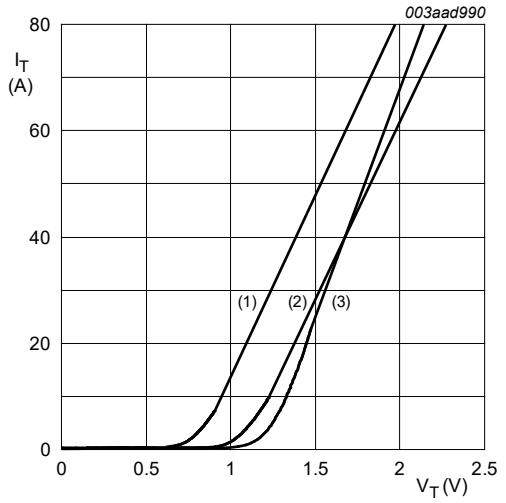



**Fig. 9. Normalized holding current as a function of junction temperature**




$V_o$ = 1.073 V; $R_s$ = 0.015 Ω
(1) $T_j$ = 125 °C; typical values
(2) $T_j$ = 125 °C; maximum values
(3) $T_j$ = 25 °C; maximum values

**Fig. 10. On-state current as a function of on-state voltage**

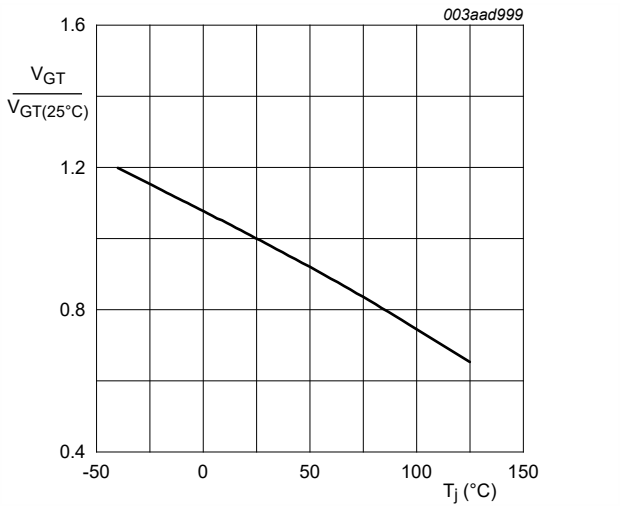
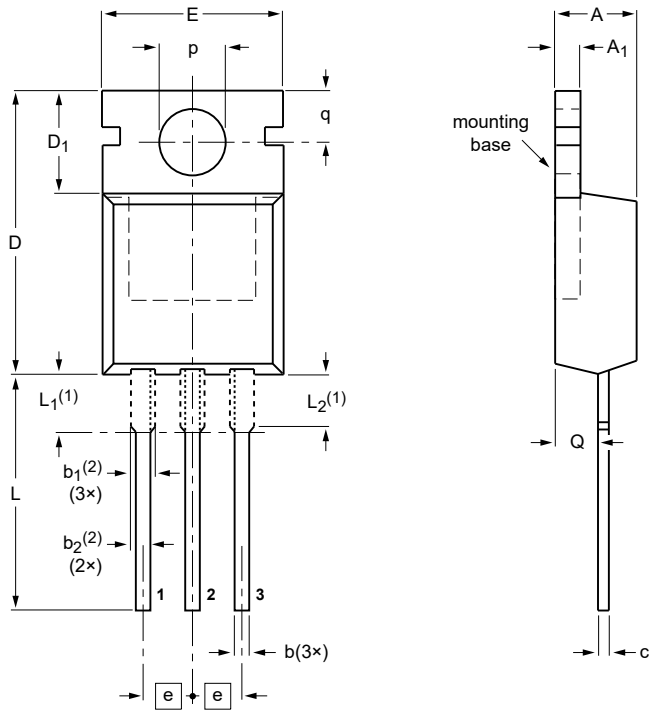



**Fig. 11. Normalized gate trigger voltage as a function of junction temperature**

## 10. Package outline

**Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB** **SOT78**




**DIMENSIONS (mm are the original dimensions)**

| UNIT | A | $A_1$ | b | $b_1$(2) | $b_2$(2) | c | D | $D_1$ | E | e | L | $L_1$(1) | $L_2$(1) max. | p | q | Q |
|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|
| mm | 4.7<br>4.1 | 1.40<br>1.25 | 0.9<br>0.6 | 1.6<br>1.0 | 1.3<br>1.0 | 0.7<br>0.4 | 16.0<br>15.2 | 6.6<br>5.9 | 10.3<br>9.7 | 2.54 | 15.0<br>12.8 | 3.30<br>2.79 | 3.0 | 3.8<br>3.5 | 3.0<br>2.7 | 2.6<br>2.2 |

**Notes**

1. Lead shoulder designs may vary.
2. Dimension includes excess dambar.

| OUTLINE VERSION | REFERENCES | | | | EUROPEAN PROJECTION | ISSUE DATE |
|---|---|---|---|---|---|---|
| | IEC | JEDEC | JEITA | | | |
| SOT78 | | 3-lead TO-220AB | SC-46 | | | ~~08-04-23~~<br>08-06-13 |

**Fig. 12. Package outline TO-220AB (SOT78)**

# 11. Legal information

## Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|---|---|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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[2] The term 'short data sheet' is explained in section "Definitions".
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## 12. Contents

1. General description....1
2. Features and benefits....1
3. Applications....1
4. Quick reference data....1
5. Pinning information....2
6. Ordering information....2
7. Limiting values....3
8. Thermal characteristics....6
9. Characteristics....7
10. Package outline....10
11. Legal information....11



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